

**WHAT IS CLAIMED IS:**

1. A stacked semiconductor device, comprising:

5           a substrate having a conductor pattern and a cavity;

          a first die received in the cavity of the cavity of the substrate and electrically  
connected to the conductor pattern via wires;

10           a second die stacked on the first die and electrically connected to the  
conductor pattern via wires, and

          an insulating layer provided on the substrate, wherein the insulating layer  
cover the first die and the second die and has a portion thereof received in the cavity to  
15   bond the first die.

2. The stacked semiconductor device as defined in claim 1, wherein the  
cavity is open at both opposite sides of the substrate.

20           3. The stacked semiconductor device as defined in claim 1, further  
comprising an adhesive layer between the first die and the second die.

          4. The stacked semiconductor device as defined in claim 3, wherein the  
insulating layer has a portion thereon attached on the substrate and the second die has a  
25   portion thereof attached on the substrate via the insulating layer.

5. The stacked semiconductor device as defined in claim 3, wherein the insulating layer covers at least a portion of the wire.

5           6. The stacked semiconductor device as defined in claim 1, wherein the first die and the second die are cross.

7. A stacked semiconductor device, comprising:

10           a substrate having a conductor pattern and a cavity;

            a first die received in the cavity of the cavity of the substrate and electrically connected to the conductor pattern via wires;

15           an adhesive layer provided on a top of the first die and received in the cavity to bond the first die;

            a second die bonded on the adhesive layer and electrically connected to the conductor pattern via wires, and

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            an insulating layer provided on the substrate, wherein the insulating layer cover the second die.

8. The stacked semiconductor device as defined in claim 7, wherein the  
25   cavity is open at both opposite sides of the substrate.

9. The stacked semiconductor device as defined in claim 7, wherein the insulating layer has a portion thereon attached on the substrate and the second die has a portion thereof attached on the substrate via the insulating layer.

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10. The stacked semiconductor device as defined in claim 7, wherein the insulating layer covers at least a portion of the wire.

11. The stacked semiconductor device as defined in claim 7, wherein the first  
10 die and the second die are cross.